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The invention relates to methods for producing semiconductor materials and can be used in semiconductor technology.

The method for removing the deformation of ZnSe single crystals in the cooling process after growth, grown from gas phase, on the plane bottom of arbitrary thickness of the closed growth chamber, consists in using the growth temperature within a range of 900...1100°C, the temperature gradient in the crystallization region 0...5°C/cm, the grown crystal crystallization and cooling embryo heating rate 20...60°C/hour using a special profile of the furnace temperature required to eliminate the effect of crystal adhesion to the walls of the ampoule.

Claims: 1

Fig.: 3